

BT138

双向可控硅
TRIAC版本号
201603-A

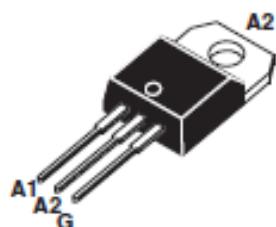
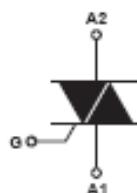
产品概述 GENERAL DESCRIPTION

BT138 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术， dv/dt 高，可靠性高，适用于控温、调光、马达控制。

BT138 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

| 参数 Parameter | 数值 Value | 单位 Unit |
|-------------------|-------------|------------|
| $I_T(RMS)$ | 12 | A |
| V_{DRM}/V_{RRM} | 600/800 | V |
| $I_{GT(HI)}$ | ≤ 10 | mA |



产品特性 FEATURES

FEATURES

- dv/dt 高
- 通态压降低
- Rohs环保产品
- Highly dv/dt
- Low on-state voltage
- Rohs Products

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

极限值(除非另有规定, $T_j=25^\circ\text{C}$) ABSOLUTE RATINGS

($T_j=25^\circ\text{C}$,unless otherwise specified)

| 符号 Symbol | 参数 Parameter | | 数值 Value | 单位 Unit |
|---------------------|--|---|-------------|------------------------|
| $I_{T(\text{RMS})}$ | RMS 通态电流 RMS on-state current (full sine wave) | $T_c=90^\circ\text{C}$ | 12 | A |
| I_{TSM} | 通态峰值浪涌电流 Non repetitive surge peak on-state current | $F=50\text{Hz}, t=20\text{ms}$ | 120 | A |
| I^2t | I^2t 耗散值 I^2t value for fusing | $T_p=10\text{ms}$ | 78 | A^2s |
| di/dt | 通态电流上升值 Critical rate of rise of on-state current | $F=120\text{Hz}, T_j=125^\circ\text{C}$ | 50 | $\text{A}/\mu\text{s}$ |
| I_{GM} | 门极峰值电流 Peak gate current | $TP=20\mu\text{s}, T_j=125^\circ\text{C}$ | 4 | A |
| $P_{G(\text{AV})}$ | 平均门极耗散功率 Average gate power dissipation | $T_j=125^\circ\text{C}$ | 1 | W |
| T_{stg} | 贮存结温范围 Storage junction temperature range | | -40~+150 | °C |
| T_j | 工作结温范围 Operating junction temperature range | | -40~+125 | °C |

电参数(除非另有规定, $T_j=25^\circ\text{C}$) ELECTRICAL CHARACTERISTICS

($T_j=25^\circ\text{C}$,unless otherwise specified)

| 参数 Parameter | 符号 Symbol | 规范值 Value | | 单位 Unit | 测试条件 Test Conditions |
|---|--------------|--------------|-----------|------------------------|--|
| | | D | E | | |
| 触发电流 Gate trigger current | I_{GT} | $I \sim III$ | ≤ 5 | mA | $V_D=12\text{V}, I_T=0.1\text{A}$ |
| | | IV | ≤ 10 | | |
| 触发电压 $C_{gate-trigger-voltage}$ | V_{GT} | ≤ 1.5 | | V | $V_D=12\text{V}, I_T=0.1\text{A}$ |
| 维持电流 $Holding\ current$ | I_H | 25 | 35 | mA | $V_D=12\text{V}, I_T=0.1\text{A}$ |
| 擎住电流 $Latching\ current$ | I_L | 40 | 50 | mA | $V_D=12\text{V}, I_T=0.1\text{A}$ |
| 电压上升率 Rise of off- state voltage | dv/dt | 50 | 200 | $\text{V}/\mu\text{s}$ | $V_D=67\% V_{DRM}$ |
| 通态压降 Peak on-state voltage | V_{TM} | ≤ 1.55 | | V | $I_T=17\text{A}$ |
| 断态漏电流 Peak repetitive forward blocking current | I_{DRM} | ≤ 10 | | μA | $V_{RRM}=V_{DRM}, T_j = 25^\circ\text{C}$ |
| | I_{RRM} | ≤ 1 | | mA | $V_{RRM}=V_{DRM}, T_j = 125^\circ\text{C}$ |

热特性 THERMAL RESISTANCES

| 符号 Symbol | 参数 Parameter | 数值 Value | 单位 Unit |
|---------------|----------------------|----------|---------|
| $R_{th(j-c)}$ | Junction to case(AC) | 1.5 | K/W |
| $R_{th(j-a)}$ | Junction to ambient | 60 | K/W |

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系

Fig.1. Maximum Power Dissipation Versus RMS On-state current

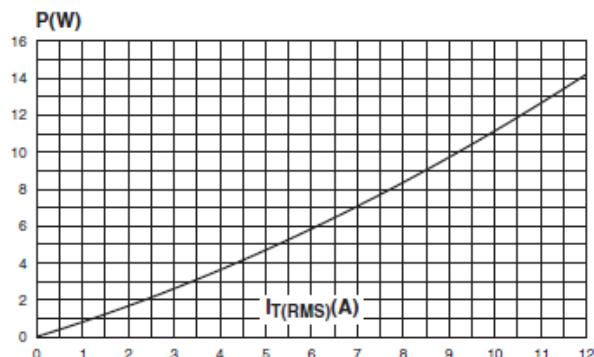


图3 通态特性

Fig.3. On-State Characteristics

图2 RMS通态电流与Tc温度关系

Fig.2. RMS On-state Current Versus Tc

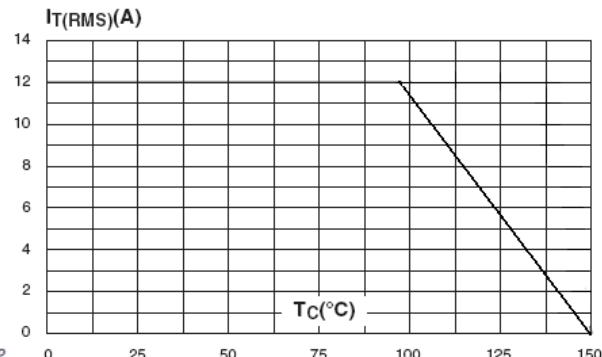


图4 通态浪涌峰值电流与周期数关系

Fig.4. Surge Peak On-state Current Versus Number Cycles

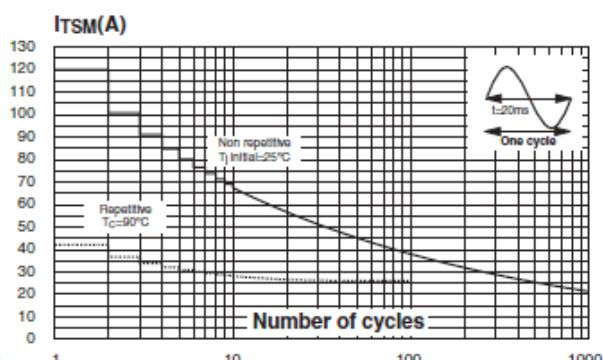
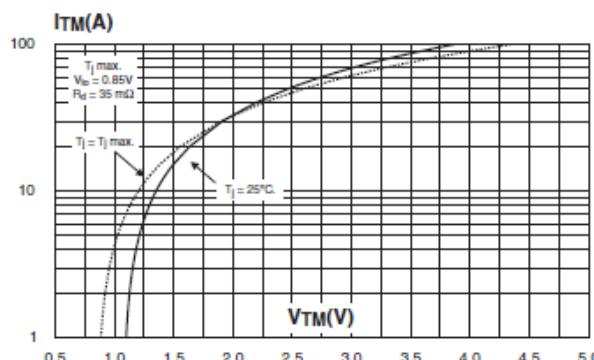
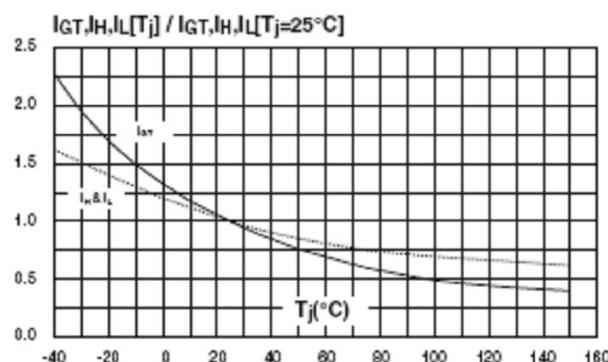


图5 IGT、IH、IL相对值（相对于25℃）与结温关系

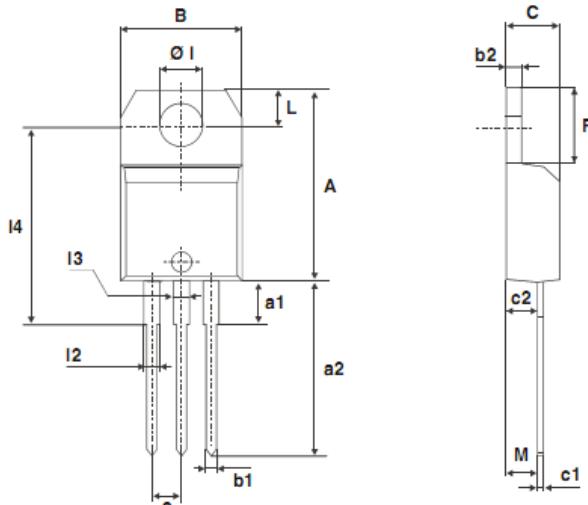
Fig.5. Relative Variation Of Gate Trigger Current

, Holding Current And Latching Current Versus Junction Temperature (Typical Value)



封装尺寸 PACKAGE MECHANICAL DATA

TO-220AB



| Ref. | Dimensions | | | | | |
|------|-------------|-------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 15.20 | | 15.90 | 0.598 | | 0.625 |
| a1 | | 3.75 | | | 0.147 | |
| a2 | 13.00 | | 14.00 | 0.511 | | 0.551 |
| B | 10.00 | | 10.40 | 0.393 | | 0.409 |
| b1 | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b2 | 1.23 | | 1.32 | 0.048 | | 0.051 |
| C | 4.40 | | 4.60 | 0.173 | | 0.181 |
| c1 | 0.49 | | 0.70 | 0.019 | | 0.027 |
| c2 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| F | 6.20 | | 6.70 | 0.244 | | 0.264 |
| ØI | 3.70 | | 3.85 | 0.146 | | 0.151 |
| I4 | 15.80 | 16.40 | 16.80 | 0.622 | 0.646 | 0.661 |
| L | 2.65 | | 2.95 | 0.104 | | 0.116 |
| I2 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| I3 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| M | | 2.60 | | | 0.102 | |

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